

## AMENDMENTS TO THE CLAIMS

1. (Original) A method comprising:  
in a wafer processing environment, introducing a liquid via a carrier gas; and  
separate from the liquid, introducing a first gas comprising ozone and a legacy amount of oxygen and a second gas comprising an effective amount of oxygen to modify a process operation.
2. (Original) The method of claim 1, wherein introducing the first gas and the second gas further comprises:  
forming the first gas; and  
after forming the first gas, combining the second gas and the first gas.
3. (Original) The method of claim 1, wherein introducing the first gas and the second gas comprises forming the first gas with the legacy amount of oxygen and the second gas.
4. (Original) The method of claim 1, wherein the wafer processing environment comprises an etching environment, and the effective amount of the second gas modifies the etch rate of an etch operation.
5. (Original) The method of claim 1, wherein the wafer processing environment comprises a film formation environment, and the effective amount of the second gas modifies the film formation.

Claims 6-13: (Canceled)